

VFT7H Series

TCVCXO

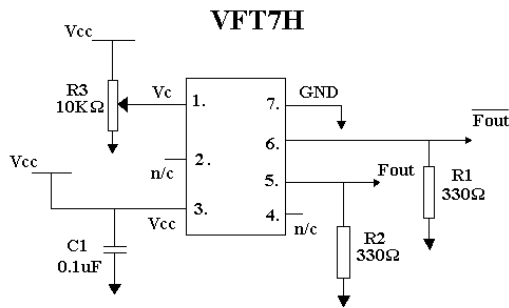
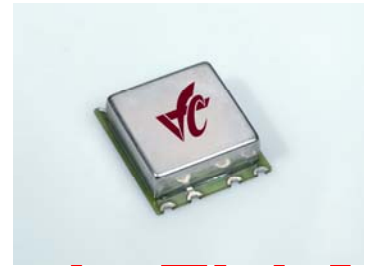
SMD High Frequency



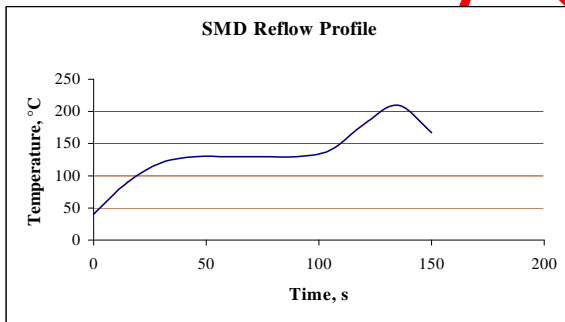
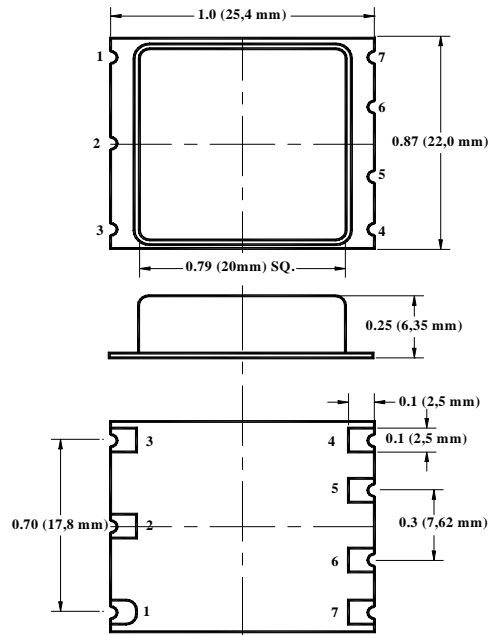
Features

***Not recommended for new designs. Please see VFTX100.**

- Small, Low Profile SMD Package
- Very Low Phase Jitter and Phase Noise
- Excellent Frequency Stability
- Low Aging, Vacuum sealed Crystal
- Ultra High Frequency – up to 1 GHz
- CMOS, Sine-Wave, or Differential PECL outputs available



- 1.) Place R1 & R2 close to the output pads.
- 2.) C1 is a power supply decoupling capacitor.
- 3.) R3 is a potentiometer used for fine tuning the output frequency.



How to Order

VFT7H

FREQUENCY, MHz

Output Type

Temperature Range

Supply Voltage

Temp. Frequency Stability

Code	Specification
C	CMOS
S	Sine-wave
E	PECL

Code	Specification
5	5V ±5%
3	3.3V ±5%

Code	Specification
A	-10°C to 60°C
B	0°C to 70°C
C	-40°C to 85°C

Code	Specification
N	±2.5 ppm
S	±1.0 ppm

Specifications

Parameter	Symb	Condition	Min	Typ	Max	Unit	Note
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VFT7H Series

TCVCO SMD High Frequency

Absolute Maximum Ratings

Input Break Down Voltage	V _{cc}		-0.5		5.5	V	
Storage temp.			-40		105	°C	
Contr. Voltage	V _c		-1		9	V	

Electrical

Frequency Range	F	CMOS Sine-wave PECL	30 30 30		160 250 1,000	MHz	
Input Voltage	V _{cc}		3.135 4.75	3.30 5.0	3.465 5.25	V	
Input Current	I _{cc}	CMOS, Sine PECL			30 100	mA	@ 100 MHz, 3.3V @ 622 MHz, 3.3V
Frequency Stab.	ΔF/F	Overall			±4.6		
Frequency Stability	ΔF/F	vs. Temperature vs. V _{cc} aging		±0.5 ±0.1 ±1 ±3.5	±1	ppm ppm/V ppm/year ppm	First Year 10 years
Calibration	ΔF/F	As shipped, 25°C		±0.5	±1	ppm	
Load		CMOS Sine PECL		15pF/10KOhm AC-coupled 50 Ohm 50 Ohm to V _{cc} -2V or Thevenin equivalent			
Duty cycle		@50%	45	50	55	%	CMOS, PECL
Rise/Fall time	Tr/Tf	20 to 80 %		2 0.35		ns	CMOS PECL
Logic "1" level	V _{oh}	CMOS	0.9V _{cc}			V	
Logic "0" level	V _{ol}	CMOS			0.1V _{cc}	V	
Logic "1" level	V _{oh}	PECL	V _{cc} -0.96		V _{cc} -0.81	V	100K available
Logic "0" level	V _{ol}	PECL	V _{cc} -1.85		V _{cc} -1.65	V	100K available
Output power		Into 50 Ohm	0	7	10	dBm	Sinewave
Start up time				2	10	ms	
Phase jitter		1□		0.4	1	ps	f _j >100 Hz
Subharmonics		PECL CMOS, Sine		-45	-40		F>250MHz
SSB Phase Noise		@10 Hz @100 Hz @1 KHz @10 KHz @100 KHz		-80 -110 -140 -150 -160		dBc/Hz	@100 MHz
SSB Phase Noise		@10 Hz @100 Hz @1 KHz @10 KHz @100 KHz		-60 -90 -120 -140 -145		dBc/Hz	@622 MHz
Input Impedance				> 10KOhm			
Control voltage	V _c		0		3.3	V	
Deviation		V _c =0V to 3.3V, 25°C	±5	±7		ppm	

Environmental and Mechanical

Operating temp. range	0°C to 70°C, -40°C to 85°C
Mechanical Shock	Per MIL-STD-202, Method 213, Cond. E
Thermal Shock	Per MIL-STD-883, Method 1011, Cond. A
Vibration	Per MIL-STD-883, Method 2007, Cond. A
Soldering Conditions	230°C for 30s Max
Hermetic Seal	Leak rate less than 5x10 ⁻⁸ atm.cc/s of helium (crystal only)

Electrical Connections

Pin Out	Pin #1- Voltage Control ; Pin #2 – N/C ; Pin #3 – V _{cc} ; Pin#4– Output, CMOS, Sine or N/C; Pin#5 – PECL Output or N/C; Pin#6 – PECL Complementary Out or N/C; Pin #7– GND
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Rev 12/08

